

AP50N06D

60V N-Channel Enhancement Mode MOSFET

Description

The AP50N06D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

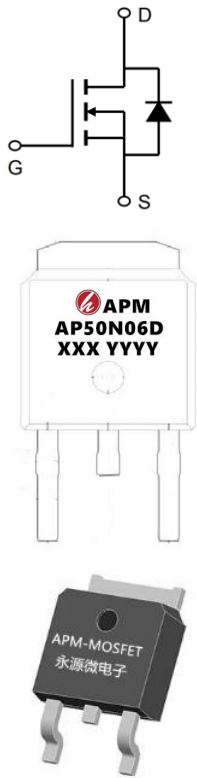
General Features

$V_{DS} = 60V$ $I_D = 50A$

$R_{DS(ON)} < 16m\Omega$ @ $V_{GS}=10V$

Application

- Battery protection
- Load switch
- Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP50N06D	TO-252-3L	AP50N06D XXXX YYYY	2500

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	60	V
VGS	Gate-Source Voltage	±20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	50	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	25	A
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7.4	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V^1$	6	A
IDM	Pulsed Drain Current ²	90	A
EAS	Single Pulse Avalanche Energy ³	39.2	mJ
IAS	Avalanche Current	28	A
$P_D@T_C=25^{\circ}C$	Total Power Dissipation ⁴	45	W
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ⁴	2	W
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
RθJA	Thermal Resistance Junction-Ambient ¹	62	°C/W
RθJC	Thermal Resistance Junction-Case ¹	2.8	°C/W

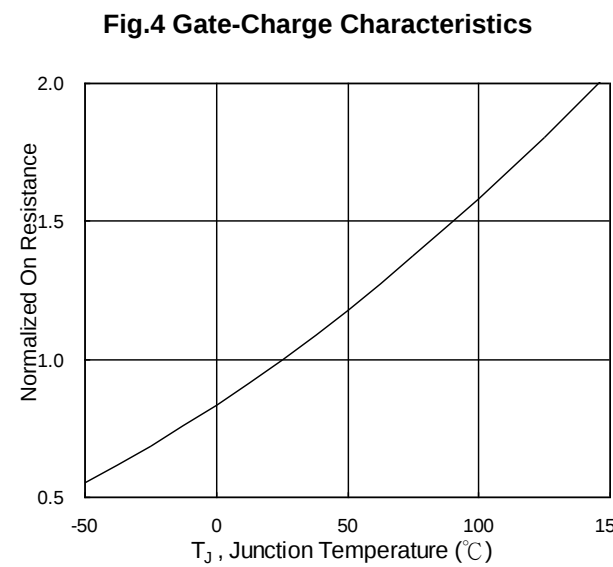
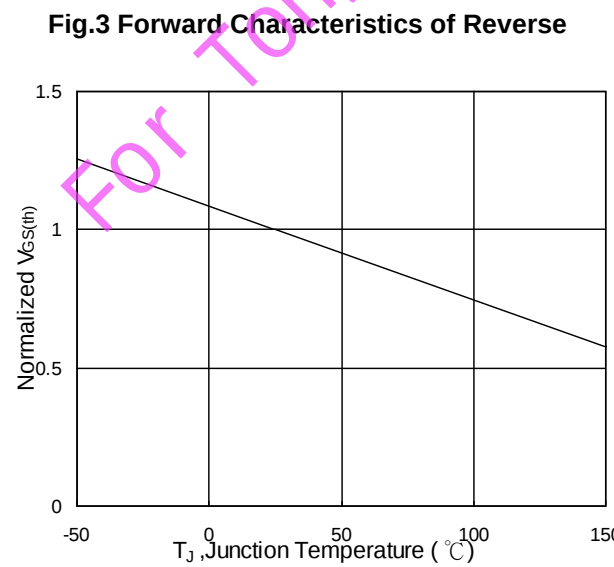
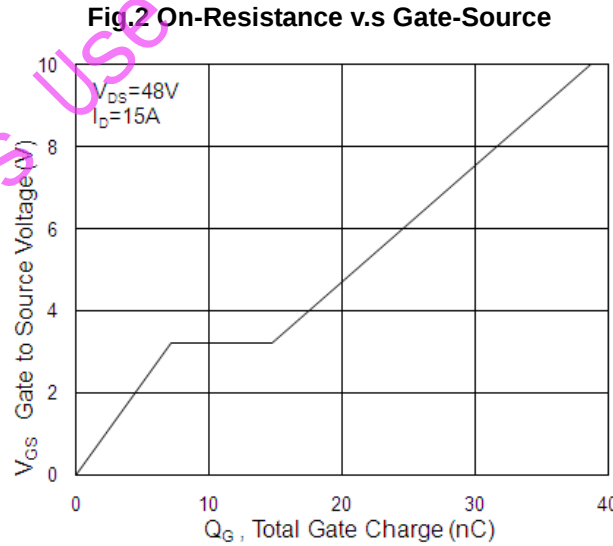
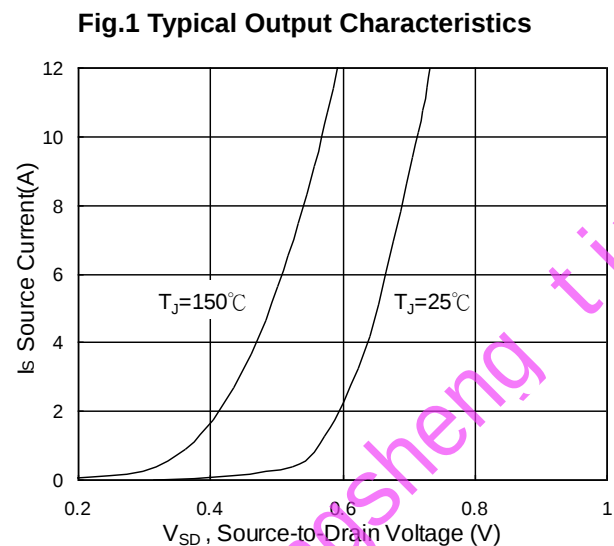
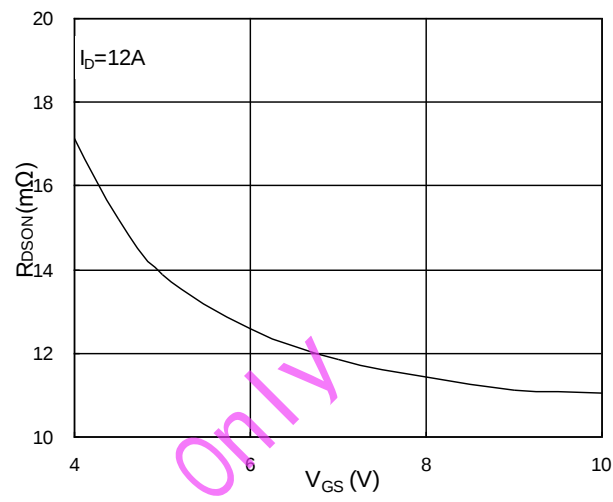
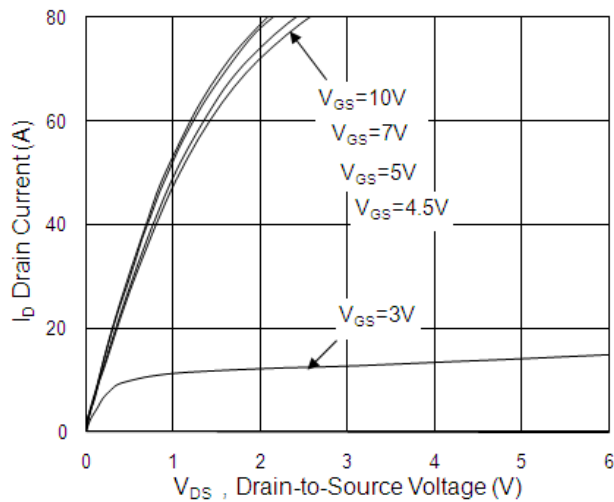
Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60	65	---	V
ΔBVDSS/ΔT _J	BVDSS Temperature Coefficient	Reference to 25°C, I _D =1mA	---	0.057	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =20A	---	11.5	16	mΩ
		V _{GS} =4.5V, I _D =10A	---	16.3	20	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.8	2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	-5.68	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =48V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =48V, V _{GS} =0V, T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V, I _D =15A	---	45	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	1.7	---	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =48V, V _{GS} =4.5V, I _D =15A	---	19.3	---	nC
Q _{gs}	Gate-Source Charge		---	7.1	---	
Q _{gd}	Gate-Drain Charge		---	7.6	---	
Td(on)	Turn-On Delay Time	V _{DD} =30V, V _{GS} =10V, R _G =3.3Ω, I _D =15A	---	7.2	---	ns
T _r	Rise Time		---	50	---	
Td(off)	Turn-Off Delay Time		---	36.4	---	
T _f	Fall Time		---	7.6	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	2423	---	pF
C _{oss}	Output Capacitance		---	145	---	
C _{rss}	Reverse Transfer Capacitance		---	97	---	
I _s	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	35	A
ISM	Pulsed Source Current ^{2,5}		---	---	80	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _S =A, T _J =25°C	---	---	1	V
t _{rr}	Reverse Recovery Time	IF=15A, dI/dt=100A/μs, T _J =25°C	---	16.3	---	nS
Q _{rr}	Reverse Recovery Charge		---	11	---	nC

Note:

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is VDD=25V, VGS=10V, L=0.1mH, IAS=28A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation

Typical Characteristics



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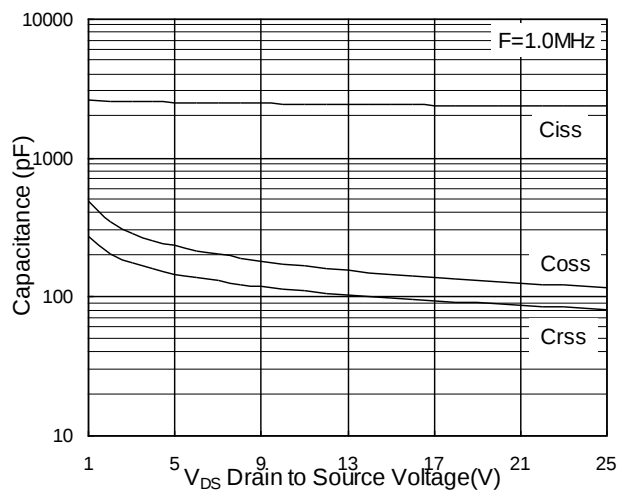


Fig.7 Capacitance

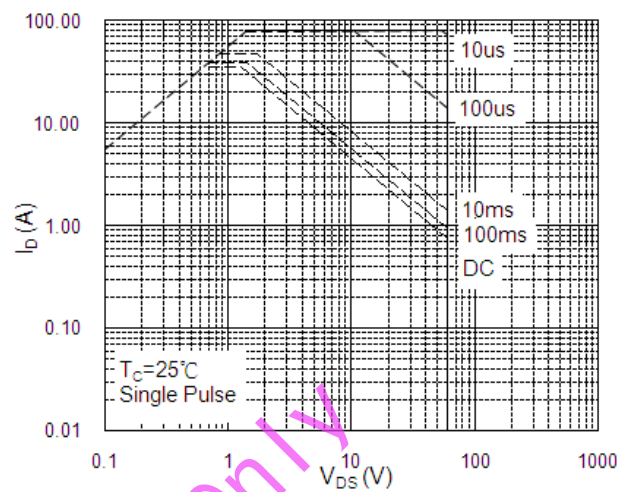


Fig.8 Safe Operating Area

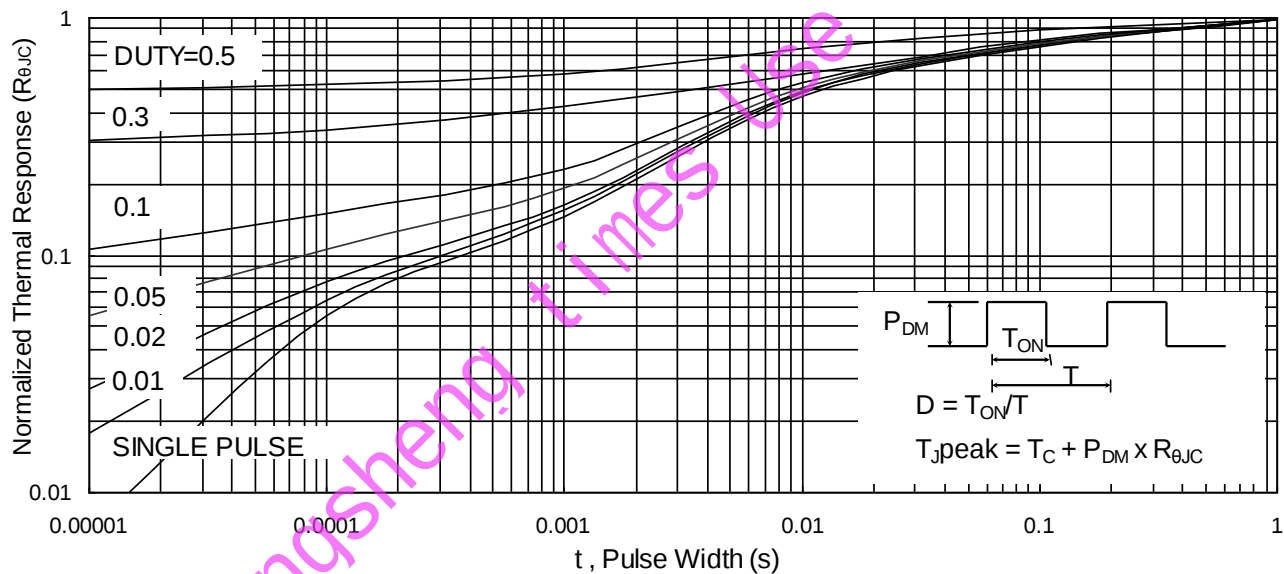


Fig.9 Normalized Maximum Transient Thermal Impedance

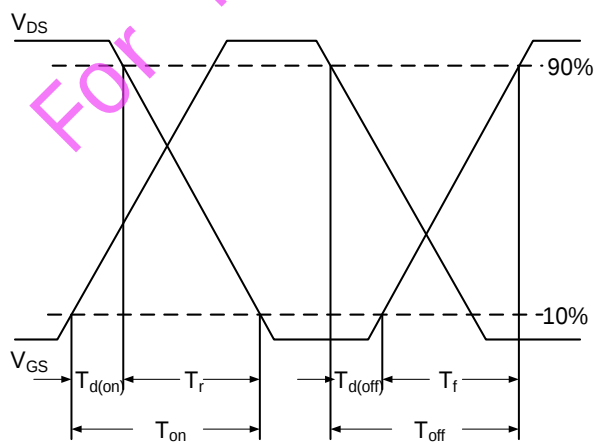


Fig.10 Switching Time Waveform

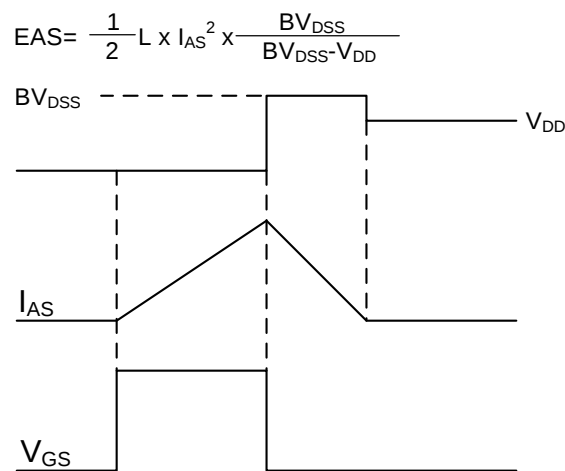
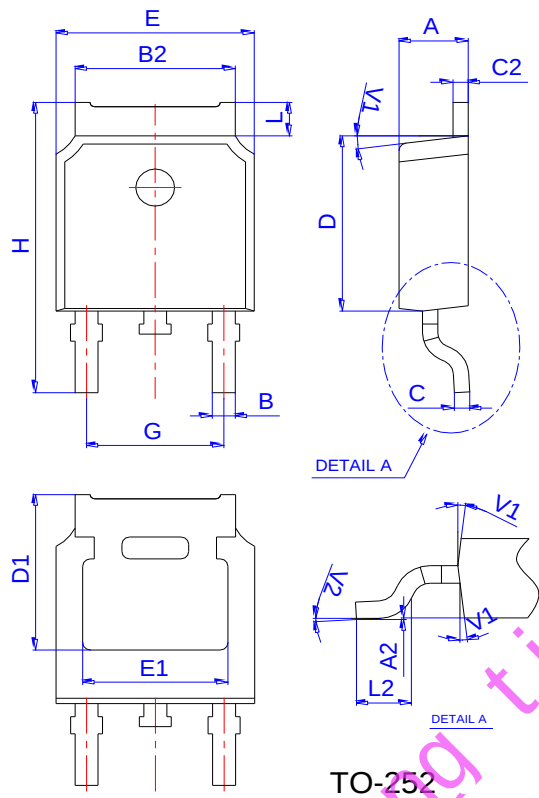


Fig.11 Unclamped Inductive Switching Waveform

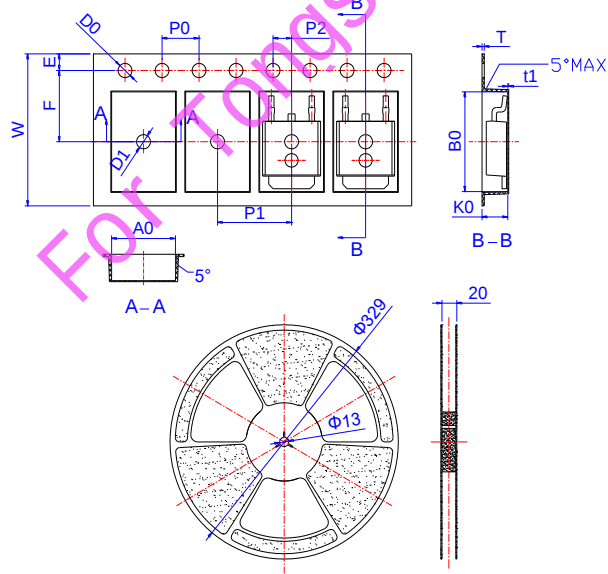
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Package Mechanical Data: TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO-252



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583

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Edition	Date	Change
Rve3.8	2018/1/31	Initial release
Rve3.9	2019/12/01	Reduce RDS(on)

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Test Report For 30PCS (30pcs 典型測試報告)

